

MOS管YJ75N75封装TO-220

产品名称	MOS管YJ75N75封装TO-220
公司名称	深圳市扬晶微电子有限公司
价格	1.10/PCS
规格参数	品牌:扬晶 型号:YJ75N75 电流100A:耐压750V
公司地址	深圳市龙华新区大浪街道和平路368号龙胜商业大厦4层K区
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产品详情

yj75n75c general description : $v_{ds} 75\text{ v}$ $i_d 100\text{ a}$ $p_d(t_c=25^\circ\text{C}) 230\text{ w}$ $r_{ds(on)typ} 10.2\text{ m}\Omega$ yj75n75c, the silicon n-channel enhanced vdmofets, is obtained by the self-aligned planar technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. the transistor can be used in various power switching circuit for system miniaturization and higher efficiency. the package form is to-220ab, which accords with the rohs standard. features : fast switching low on resistance($r_{dson} 11.5\text{ m}\Omega$) low gate charge (typical data:71nc) low reverse transfer capacitances(typical:40pf) 100% single pulse avalanche energy test applications : automotive、dc motor control and class d amplifier. absolute ($t_c=25^\circ\text{C}$ unless otherwise specified) : symbol parameter rating units v_{ds} drain-to-source voltage 75 v continuous drain current 100 a i_d continuous drain current $t_c = 100^\circ\text{C}$ 71 a i_{dm} a1 pulsed drain current 400 a v_{gs} gate-to-source voltage $\pm 20\text{ v}$ e_{as} a2 single pulse avalanche energy 1100 mj e_{ar} a1 avalanche energy ,repetitive 100 mj i_{ar} a1 avalanche current 4.5 a dv/dt a3 peak diode recovery dv/dt 5.0 v/ns power dissipation 230 w p_d derating factor above 25°C 1.53 w/ t_j , t_{stg} operating junction and storage temperature range 175°C , -55 to 175°C t_l maximum temperature for soldering 300°C s h enzheng yangjing micro-electronics co.,ltd. to-220 ab plastic-encapsulate mosfets 深圳市扬晶微电子有限公司是一家二、三极管，高低压mos管生产厂商。

主推mos型号有：

1n60, 2n60, 4n60,5n60,7n60,8n60,10n60,12n60,75n75

si2300, si2301, si2302,ao3400,ao3401, ao3402,ao3407

9926,9435,4435,4953,8205,dw01等众多型号。全新yj原装，

质量稳定，单价优势，欢迎来电订购。